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## Rare-earth chromium gallides RE<sub>4</sub>CrGa<sub>12</sub> (RE=Tb-Tm)

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#### ABSTRACT

The ternary rare-earth-metal chromium gallides  $RE_4\text{CrGa}_{12}$  (RE=Tb-Tm) have been prepared by reactions of the elements at 1000 °C in the presence of excess gallium used as a self-flux. Their structures are derived by inserting Cr atoms into a quarter of the empty  $Ga_6$  octahedral clusters found in the parent binary gallides  $REGa_3$  (AuCu<sub>3</sub>-type), although single-crystal X-ray diffraction studies suggest that complex superstructures may be adopted. An ideal ordered  $Y_4\text{PdGa}_{12}$ -type structure was successfully refined for a crystal of  $Dy_4\text{CrGa}_{12}$  (Pearson symbol cI34, space group  $Im\overline{3}m$ , Z=2, a=8.572(1) Å). Magnetic measurements on single-crystal samples reveal ferromagnetic or possibly ferrimagnetic ordering for the Tb, Dy, and Er members ( $T_c=22$ , 15, and 2.8 K, respectively) and antiferromagnetic ordering for the Ho member ( $T_N=7.5$  K). Band structure calculations on a hypothetical " $Y_4\text{CrGa}_{12}$ " model suggest that the Cr atoms carry no local magnetic moment.

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#### 1. Introduction

Binary rare-earth-metal trigallides REGa<sub>3</sub> with the cubic  $AuCu_3$ -type structure are known for RE=Sc, Tb-Tm, Lu, U, and Np [1-5]. This simple structure, with RE atoms at the corners and Ga atoms at the face centers of the cubic unit cell, features a vacant octahedral site at the body center that is  $\sim$  2.1 Å (half the cell length) distant from the surrounding Ga atoms. The interstitial site can be filled to various degrees by guest atoms M. Full occupation to give a perovskite (CaTiO<sub>3</sub>-type) structure with the formulation REMGa<sub>3</sub> has not been observed, although the inverse structures  $RE_3GaX$  (X=C, N) are known [6.7]. Half occupation to give a K<sub>2</sub>PtCl<sub>6</sub>-type structure is found in RE<sub>2</sub>MnGa<sub>6</sub> [8]. By far the most common scenario is quarter occupation to give a Y<sub>4</sub>PdGa<sub>12</sub>type structure, which forms for RE<sub>4</sub>MGa<sub>12</sub> (M=Fe, Ni, Pd, Pt, Ag) [9-14] as well as the uranium analogs  $U_4MGa_{12}$  (M=Fe, Co, Rh, Ni, Pd) [15-18] and quaternary mixed gallide-germanides  $RE_4M_{1-x}Ga_{12-y}Ge_y$  (M=Mn, Fe) [19,20]. It may also be possible for the occupation to vary continuously, as suggested by the homogeneity range of x=0-0.3 in TmMn<sub>x</sub>Ga<sub>3</sub> [21].

The primary interest in the quarter-occupied gallides  $RE_4MGa_{12}$  and related compounds rests in their magnetic properties. Most representatives whose magnetic properties have been measured (largely the M=Fe, Pd, and Pt members) display antiferromagnetic ordering [11,12,14,19]. The effective magnetic

moments appear to have no contributions from the transitionmetal atoms M, implying that they form completely filled d-bands well below the Fermi level. Ferromagnetic ordering can be induced through substitution with an earlier transition metal, which is more likely to give partially filled d-bands crossed by the Fermi level, as shown in  $Y_4Mn_{1-x}Ga_{12-y}Ge_y$ , whose Curie temperature can be modified through doping [20].

In the course of investigating ternary gallide systems RE-M-Ga containing earlier transition metals, we have identified the series  $RE_4$ CrGa<sub>12</sub> (RE=Tb-Tm). We report here their crystal growth and magnetic properties, and discuss their bonding and electronic structure analyzed through band structure calculations.

#### 2. Experimental

#### 2.1. Synthesis

Starting materials were RE pieces (99.9%, Hefa), Cr powder (99%, Alfa-Aesar), and Ga pieces (99.99%, Cerac). Substitutional reactions with different RE metals established that  $RE_4$ CrGa<sub>12</sub> forms for RE=Tb-Tm but not for RE=Y, Sm, Gd, Yb, and Lu. Although arc-melting of stoichiometric mixtures (4 RE+Cr+12 Ga) followed by annealing at 1000 °C over 2 weeks was attempted, no suitable single crystals could be obtained from this method and the products were not single-phase. Because the ternary gallides  $RE_4$ CrGa<sub>12</sub> possess a crystal structure derived from that of the binary gallides  $REGa_3$ , their powder X-ray diffraction patterns are very similar. Moreover, crystals of

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REGa<sub>3</sub> and RE<sub>4</sub>CrGa<sub>12</sub> are indistinguishable in their cubic habits. It is thus especially important to characterize RE<sub>4</sub>CrGa<sub>12</sub> in the form of single-crystal samples. In lieu of the arc-melting procedure, the elements were reacted directly in the presence of excess Ga acting as a self-flux (4 RE+Cr+30 Ga), in alumina crucibles placed within fused-silica tubes which were then evacuated and sealed. The tubes were heated at 1000 °C for 7 h, cooled to 850 °C over 2 h, and cooled to 250 °C over 50 h. At this point, the tubes were removed from the furnace and centrifuged to spin off the Ga flux from the product. Any remaining flux was removed by sonication in ethanol followed by treatment with 3 M I<sub>2</sub> in DMF over 12 h. This procedure yielded small crystals (typically < 0.5 mm in their longest dimensions) (Fig. S1 in Supplementary Data) from which specimens were selected for single-crystal X-ray diffraction analysis. Energy-dispersive X-ray (EDX) analysis on these crystals on a Zeiss EVO MA 15 or a JEOL JSM-6010LA scanning electron microscope confirmed the presence of all three elements in proportions (26(2)% RE, 4(2)% Cr, 70(3)% Ga) that agree well with expectations (24% RE, 6% Cr, 70% Ga). To obtain larger crystals for magnetic measurements, the syntheses were repeated as before except that the tubes were held at 850 °C for 7 h and cooled to 250 °C over 84 h. The slower cooling rate yielded larger crystals ( > 0.5 mm) confirmed by EDX analysis to have uniform composition (Fig. S2 in Supplementary Data). These crystals were generally fractured and thus unsuitable for single-crystal diffraction analysis, but they were adequate for magnetic measurements, after which they were analyzed by powder X-ray diffraction (vide infra).

#### 2.2. Structure determination

Single crystals of  $RE_4$ CrGa<sub>12</sub> were selected only after they were confirmed by EDX analysis to be the ternary compounds and not binary gallides for which they are easily mistaken by visual inspection alone. Intensity data were collected at 295 K on a Bruker Platform/SMART 1000 or a Bruker D8/SMART APEX II diffractometer equipped with Mo  $K\alpha$  radiation source. Faceindexed numerical absorption corrections were applied. Structure solution and refinement were carried out with use of the SHELXTL (version 6.12) program package [22].

Numerous crystals examined revealed intense reflections corresponding to a  $\sim$ 4 Å cubic subcell and weaker reflections indexed to  $\sim$  17 Å cubic supercell (Fig. S3 in Supplementary Data). In the subcell, a structural model with the formulation "RECr<sub>0.25</sub>Ga<sub>3</sub>" in space group  $Pm\overline{3}m$  (no. 221) can be proposed with RE in 1b (½, ½,  $\frac{1}{2}$ ), quarter-occupied Cr in 1a (0, 0, 0), and Ga in 3d ( $\frac{1}{2}$ , 0, 0). Although this model gave satisfactory residuals (R(F) < 0.05), the Cr sites are coordinated octahedrally by Ga atoms at unphysically short distances of 2.1-2.2 Å. This could be corrected by introducing deficiencies in the Ga sites and allowing the Cr occupancy to vary (i.e., " $RECr_xGa_{3-y}$ "), but we note the good agreement of the EDX analyses to the ideal formulation RE4MGa12 which is generally found for other transition-metal substituents M. Any model proposed in the cubic subcell must necessarily place symmetry-equivalent Cr atoms in the centers of all Ga<sub>6</sub> octahedra, which are linked by corner-sharing, and no amount of distortion in these octahedra can alleviate the unphysically short Cr-Ga distances.

Transformation to larger supercells, either by doubling to  $a = \sim 8$  Å or quadrupling to  $a = \sim 17$  Å, permits multiple Cr sites to be introduced in the structural models with more reasonable 2.4–2.5 Å distances to surrounding Ga atoms. Unfortunately, the difference electron density maps invariably revealed additional Cr sites that suffered from the same short Cr–Ga distances, and we were unable to improve the refinements much further (R(F) > 0.15 with substantial remaining difference electron density), whatever cubic space group was attempted. There is now emerging evidence in the

literature that related *RE*<sub>4</sub>*MG*a<sub>12</sub> compounds can exhibit highly complex modulated structures associated with long-range ordering of *M* vacancies [20]. In effect, *REG*a<sub>3</sub> and *RE*<sub>4</sub>*MG*a<sub>12</sub> can easily form

**Table 1**Comparison of cell parameters for RE<sub>4</sub>CrGa<sub>12</sub> and REGa<sub>3</sub> (RE=Tb-Tm) <sup>a</sup>.

	Tb <sub>4</sub> CrGa <sub>12</sub>	Dy <sub>4</sub> CrGa <sub>12</sub>	Ho <sub>4</sub> CrGa <sub>12</sub>	Er <sub>4</sub> CrGa <sub>12</sub>	Tm <sub>4</sub> CrGa <sub>12</sub>
a (Å)	17.126(2)	17.072(1)	17.120(1)	16.964(1)	16.894(1)
a/4 (Å)	4.282(1)	4.268(1)	4.280(1)	4.241(1)	4.224(1)
V (Å <sup>3</sup> )	5023(2)	4975(1)	5018(1)	4882(1)	4822(1)
V/64 (Å <sup>3</sup> )	78.48(3)	77.74(1)	78.40(2)	76.28(1)	75.34(2)
	TbGa <sub>3</sub>	DyGa <sub>3</sub>	HoGa <sub>3</sub>	ErGa <sub>3</sub>	$TmGa_3$
a (Å)	4.285(1)	4.271(1)	4.235(1)	4.219(1)	4.202(1)
V (Å <sup>3</sup> )	78.68(5)	77.91(5)	75.96(5)	75.10(5)	74.19(5)

<sup>&</sup>lt;sup>a</sup> Cell parameters for  $REGa_3$ , obtained from powder XRD data for RE=Tb, Dy, Er, Tm and single-crystal data for RE=Ho, are taken from Ref. [2].

**Table 2**Crystallographic data for Dy<sub>4</sub>CrGa<sub>12</sub>.

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Data collection and refinement				
Formula	Dy <sub>4</sub> CrGa <sub>12</sub>			
Formula mass (amu)	1538.64			
Space group	$Im\overline{3}m$ (No. 229)			
a (Å)	8.572(1)			
• •				
$V(Å^3)$	629.9(2)			
Z	2			
$\rho_{\rm calcd}$ (g cm <sup>-3</sup> )	8.113			
T(K)	295(2)			
Crystal dimensions (mm)	0.11 × 0.06 × 0.06			
Radiation	Graphite monochromated Mo $K\alpha$ ,			
a1.	$\lambda = 0.71073 \text{ Å}$			
$\mu(\text{Mo }K\alpha) \text{ (mm}^{-1})$	49.34			
Transmission factors	0.042-0.154			
$2\theta$ limits	6.72-65.88°			
Data collected	$-13 \le h \le 12, -12 \le k \le 12, -13 \le l \le 13$			
No. of data collected	4290			
No. of unique data, including	146 ( $R_{\text{int}}$ =0.059)			
$F_0^2 < 0$ No. of unique data, with	128			
$F_0^2 > 2\sigma(F_0^2)$	126			
No. of variables	10			
$R(F)$ for $F_o^2 > 2\sigma(F_o^2)^a$	0.022			
$R_{\rm w}(F_{\rm o}^2)^{\rm b}$	0.064			
Goodness of fit	1.23			
$(\Delta \rho)_{\rm max}$ , $(\Delta \rho)_{\rm min}$ (e Å <sup>-3</sup> )	2.49, -2.51			
$(\Delta \rho)_{\rm max}$ , $(\Delta \rho)_{\rm min}$ (e A )	2.13, 2.31			
Positional and displacement parameters <sup>c</sup>				
Dy at 8c (¼, ¼, ¼)				
$U_{\rm eq}$ (Å <sup>2</sup> )	0.0095(3)			
Cr at 2a (0, 0, 0)				
$U_{\rm eq}$ ( $\mathring{\rm A}^2$ )	0.0131(9)			
Ga1 at 12e (x, 0, 0)				
X	0.2895(2)			
$U_{\rm eq}$ (Å <sup>2</sup> )	0.0119(3)			
Ga2 at 12d (¼, 0, ½)	•			
$U_{\text{eq}}(\mathring{A}^2)$	0.0105(3)			
O <sub>eq</sub> (A )	0.0100(3)			
Interatomic distances (Å)				
Dy-Ga2 ( × 6)	3.0307(5)			
Dy-Ga1 ( × 6)	3.0495(5)			
Cr-Ga1 ( × 6)	2.482(2)			
Ga1-Ga2 ( × 4)	2.802(1)			
$Ga2-Ga2 (\times 4)$	3.031(1)			

$$<sup>\</sup>label{eq:resolvent} \begin{split} ^{a}R(F) &= \sum ||F_{o}| - |F_{c}|| / \sum |F_{o}| \; . \\ ^{b}R_{w}\Big(F_{o}^{2}\Big) &= \left[\sum \left[w\Big(F_{o}^{2} - F_{c}^{2}\Big)^{2}\right] / \sum wF_{o}^{4}\right]^{1/2} \; ; \; w^{-1} = \left[\sigma^{2}\Big(F_{o}^{2}\Big) + (Ap)^{2} + Bp\right] \; \text{where} \\ p &= \left[\max\Big(F_{o}^{2}, 0\Big) + 2F_{c}^{2}\right] / 3. \end{split}$$

 $<sup>\</sup>overset{c}{\circ}$   $U_{\text{eq}}$  is defined as one-third of the trace of the orthogonalized  $U_{ij}$  tensor.

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